ABSTRACT

Assist Features for use in Lithographic Projection

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   In a mask pattern for a device such as a DRAM including a nearly regular array of
isolated features, assist features are positioned so as to make the array more symmetric. Where
the isolated features are positioned at most but not all of the points of a regular unit cell, the
assist features may be positioned at the points of the unit cell not occupied by the isolated

10   features. The isolated features may represent contact holes.